

### Description

The SX15H06S uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

$V_{DS} = 60V$   $I_D = 15A$

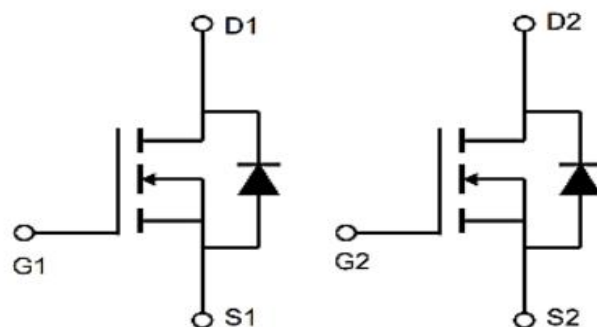
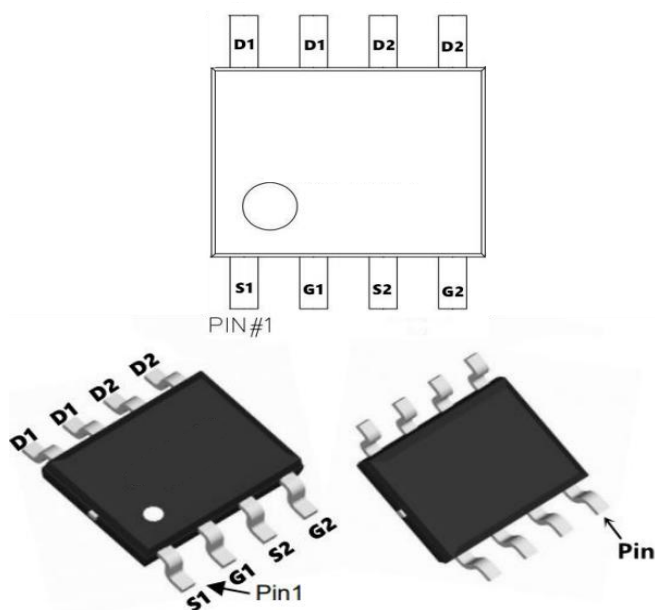
$R_{DS(ON)} < 18m\Omega$  @  $V_{GS}=10V$

### Application

Battery protection

Load switch

Uninterruptible power supply



### Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D @ T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	9.2	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	45	A
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	64	mJ
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	3.6	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	85	$^\circ\text{C/W}$

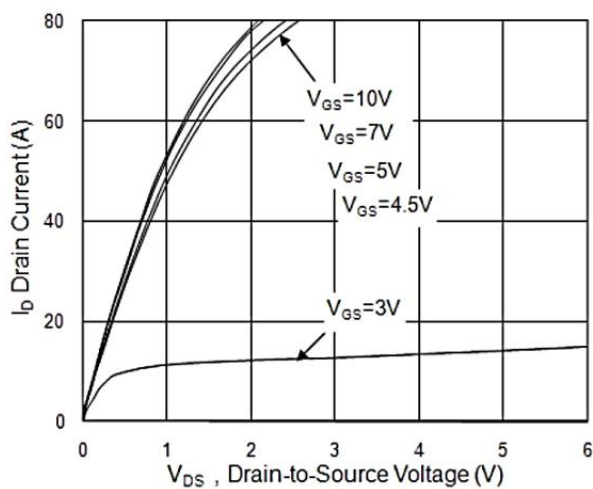
**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	65	---	V
ΔBVDSS/ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.057	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =12A	---	11	18	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	15	20	
VGS(th)	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-5.68	---	mV/°C
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =15A	---	45	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.7	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =48V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	---	19.3	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	7.1	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	7.6	---	
Td(on)	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =15A	---	7.2	---	ns
T <sub>r</sub>	Rise Time		---	50	---	
Td(off)	Turn-Off Delay Time		---	36.4	---	
T <sub>f</sub>	Fall Time		---	7.6	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	2423	---	pF
C <sub>oss</sub>	Output Capacitance		---	145	---	
Crss	Reverse Transfer Capacitance		---	97	---	
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	35	A
ISM	Pulsed Source Current <sup>2,5</sup>		---	---	80	A
VSD	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =A, T <sub>J</sub> =25°C	---	---	1	V
t <sub>rr</sub>	Reverse Recovery Time	IF=15A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	16.3	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	11	---	nC

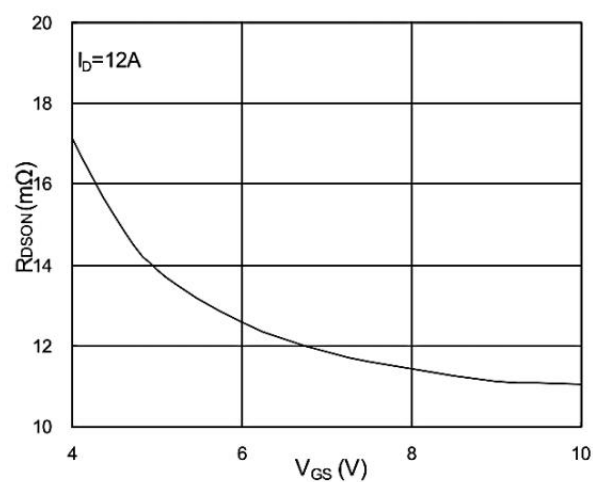
**Notes:**

- 1、The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2、The data tested by pulsed, pulse width .The EAS data shows Max. rating .
- 3、The power dissipation is limited by 175°C junction temperature
- 4、The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

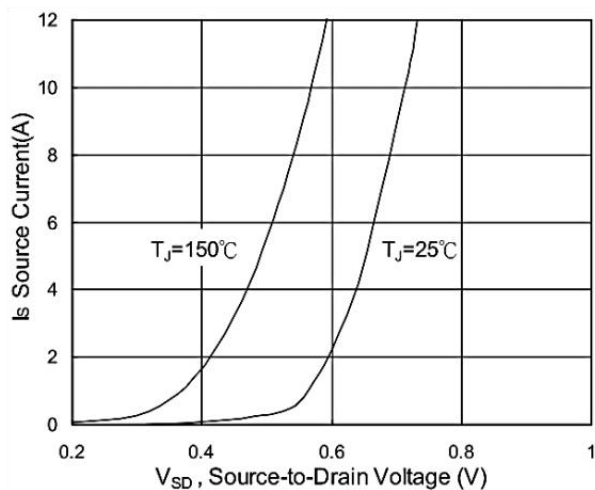
## Typical Characteristics



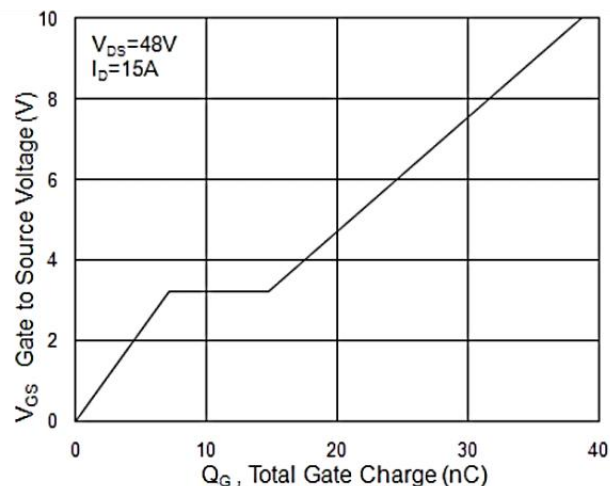
**Fig.1 Typical Output Characteristics**



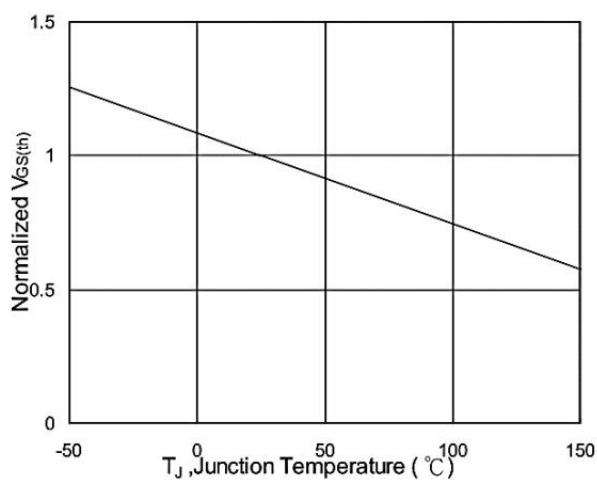
**Fig.2 On-Resistance v.s Gate-Source**



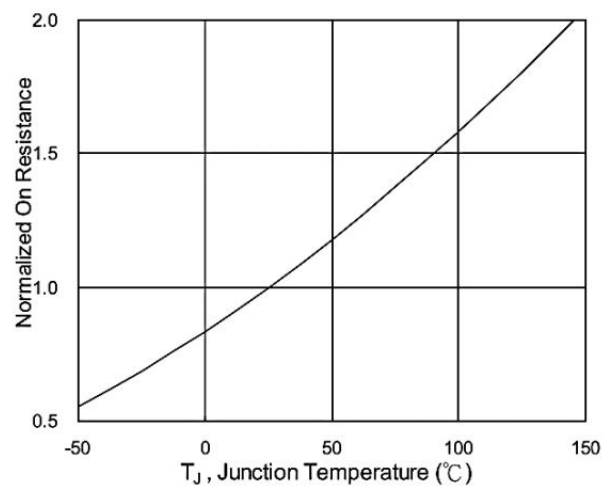
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**

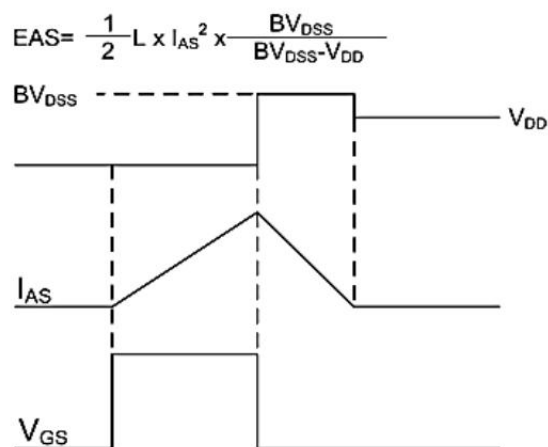
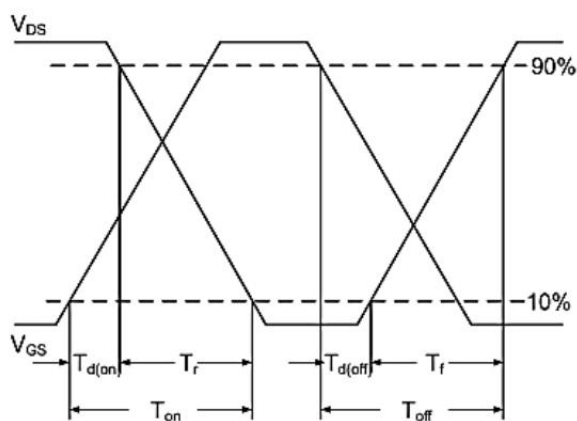
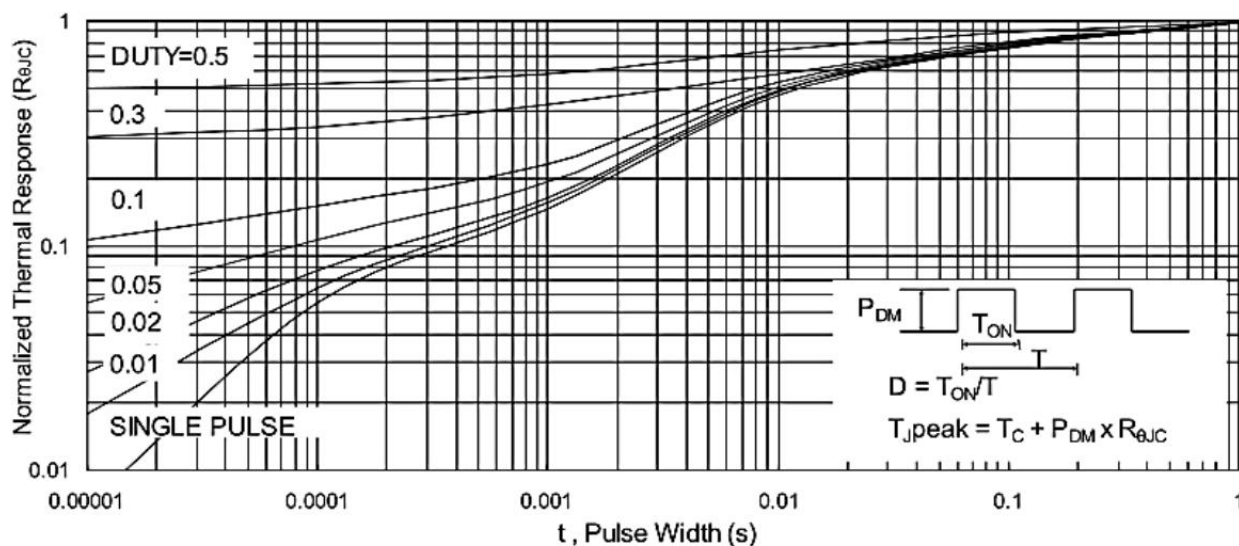
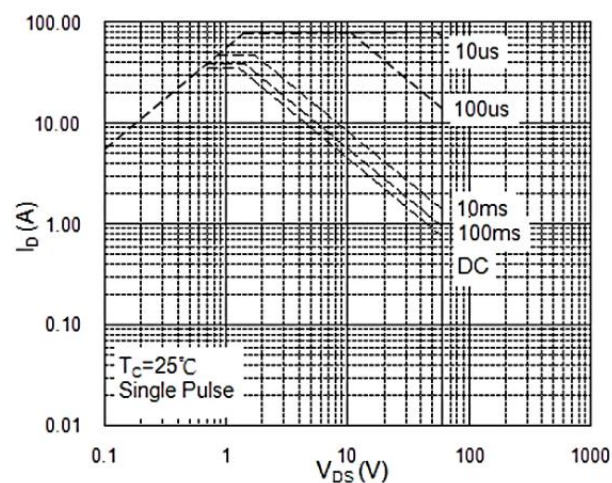
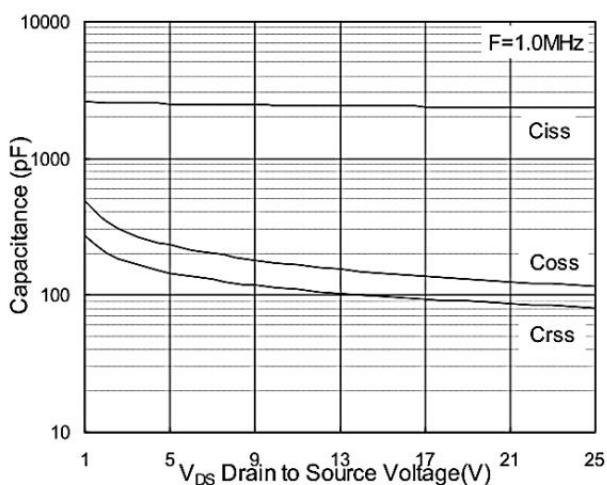


**Fig.5 Normalized  $V_{GS}$  v.s  $T_J$**

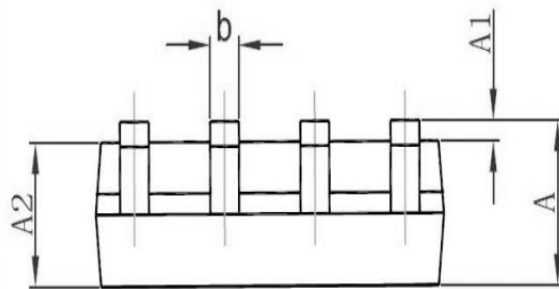
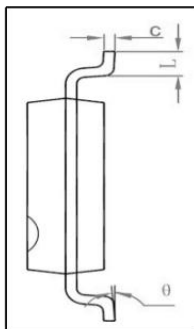
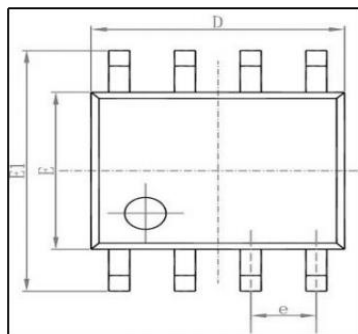


**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**

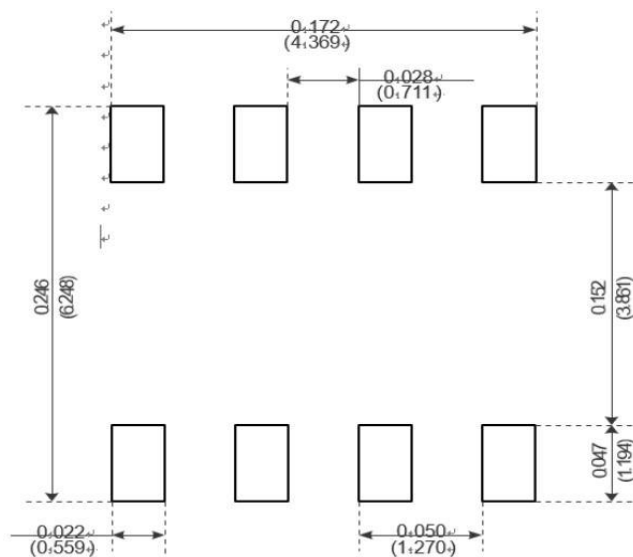
## Typical Characteristics



## Package Mechanical Data-SOP-8L-DX-Double



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOP-8L		3000